

ABSTRACT OF THE DISCLOSURE

A TFT is formed on an insulating substrate, and a photosensitive resin film as an interlayer insulating film is formed so as to cover the TFT. A first photomask and a second photomask provided with scattered circular light-shielding portions are used to perform two exposure so that contact holes are formed in the photosensitive resin and smooth concave and convex portions in regions other than the TFT. Further, an MoN film and a reflective electrode are successively laminated on the photosensitive resin. The N2 content in the MoN film is made between 5 atomic % and 30 atomic % inclusive so that the MoN film can obtain strong adhesion to the photosensitive resin and prevent decrease in the etching rate.

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